

# MJL4281A (NPN) MJL4302A (PNP)

Preferred Device

## Complementary NPN-PNP Silicon Power Bipolar Transistors

The MJL4281A and MJL4302A are PowerBase™ power transistors for high power audio.

- 350 V Collector–Emitter Sustaining Voltage
- Gain Complementary:
  - Gain Linearity from 100 mA to 5 A
  - High Gain – 80 to 240
  - $h_{FE} = 50$  (min) @  $I_C = 8$  A
- Low Harmonic Distortion
- High Safe Operation Area – 1.0 A/100 V @ 1 Second
- High  $f_T$

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	350	Vdc
Collector–Base Voltage	$V_{CBO}$	350	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector–Emitter Voltage – 1.5 V	$V_{CEX}$	350	Vdc
Collector Current – Continuous – Peak (Note 1)	$I_C$	15 30	Adc
Base Current – Continuous	$I_B$	1.5	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	230 1.84	Watts $^\circ\text{C}/\text{W}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	– 65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.54	$^\circ\text{C}/\text{W}$

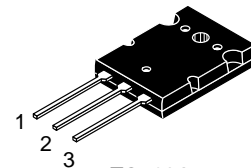
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.



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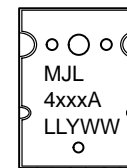
<http://onsemi.com>

**15 AMPERES  
COMPLEMENTARY  
SILICON POWER  
TRANSISTORS  
350 VOLTS  
230 WATTS**



TO-264  
CASE 340G  
STYLE 2

### MARKING DIAGRAM



1 BASE                      3 EMITTER  
2 COLLECTOR

MJL4xxxA = Device Code  
xxx        = 281 OR 302  
LL         = Location Code  
Y          = Year  
WW       = Work Week

### ORDERING INFORMATION

Device	Package	Shipping
MJL4281A	TO-264	25 Units/Rail
MJL4302A	TO-264	25 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

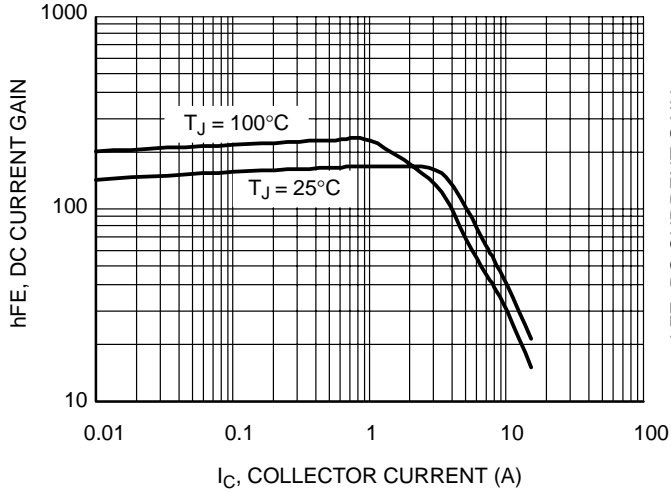
## MJL4281A (NPN) MJL4302A (PNP)

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

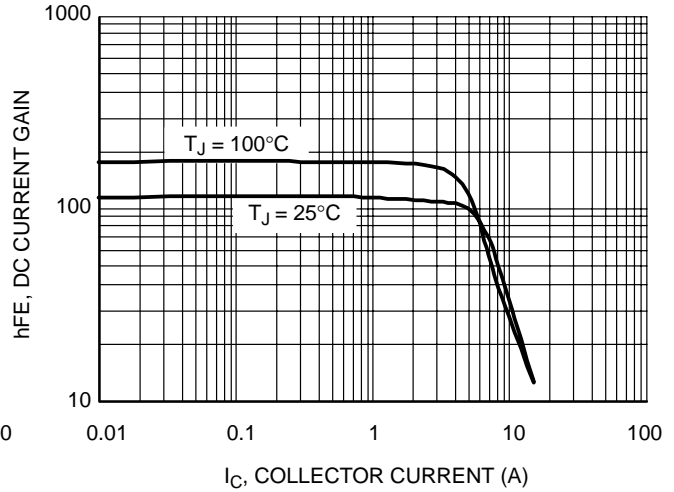
Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector Emitter Sustaining Voltage (I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0)	V <sub>CE(sus)</sub>	350		Vdc
Collector Cut-off Current (V <sub>CE</sub> = 200 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>		100	μAdc
Collector Cutoff Current (V <sub>CB</sub> = 350 Vdc, I <sub>E</sub> = 0)	I <sub>CB0</sub>	–	50	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	5.0	μAdc
<b>SECOND BREAKDOWN</b>				
Second Breakdown Collector with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 1.0 s (non-repetitive) (V <sub>CE</sub> = 100 Vdc, t = 1.0 s (non-repetitive)	I <sub>S/b</sub>	4.5 1.0	– –	Adc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 15 Adc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	80 80 80 80 50 10	250 250 250 250 – –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc)	V <sub>CE(sat)</sub>	–	1.0	Vdc
Emitter–Base Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 A)	V <sub>BE(sat)</sub>	–	1.4	Vdc
Base–Emitter ON Voltage (I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE(on)</sub>	–	1.5	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 5.0 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	35	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1.0 MHz)	C <sub>ob</sub>	–	600	pF

# MJL4281A (NPN) MJL4302A (PNP)

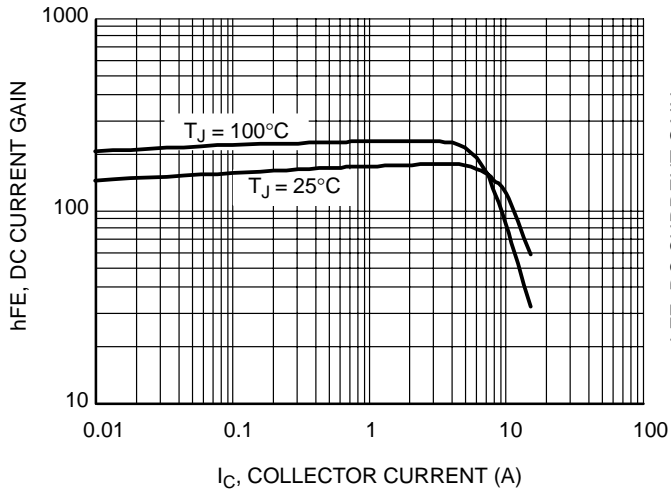
## TYPICAL CHARACTERISTICS



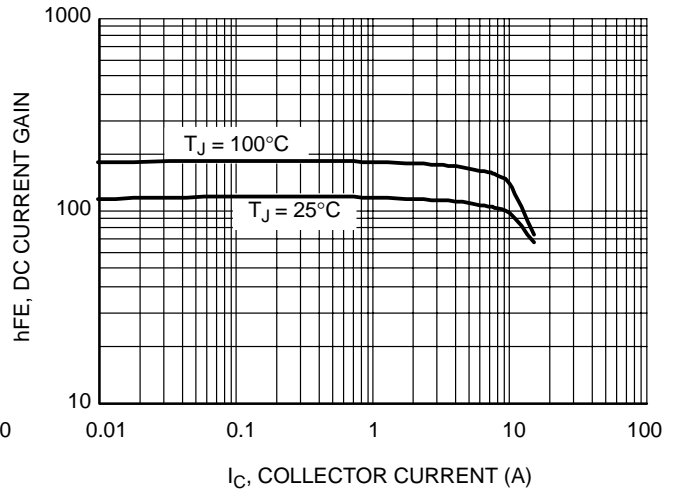
**Figure 1. DC Current Gain,  $V_{CE} = 5$  V, NPN MJL4281A**



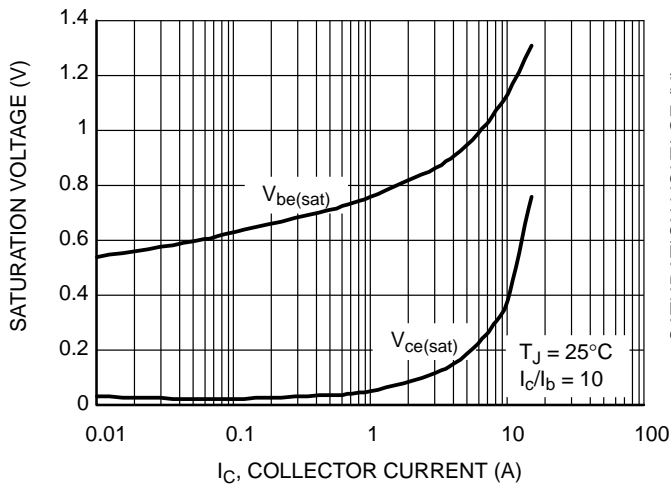
**Figure 2. DC Current Gain,  $V_{CE} = 5$  V, PNP MJL4302A**



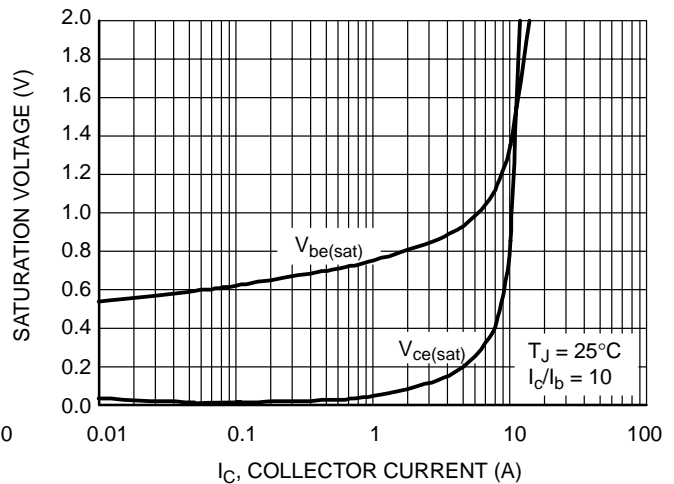
**Figure 3. DC Current Gain,  $V_{CE} = 20$  V, NPN MJL4281A**



**Figure 4. DC Current Gain,  $V_{CE} = 20$  V, PNP MJL4302A**



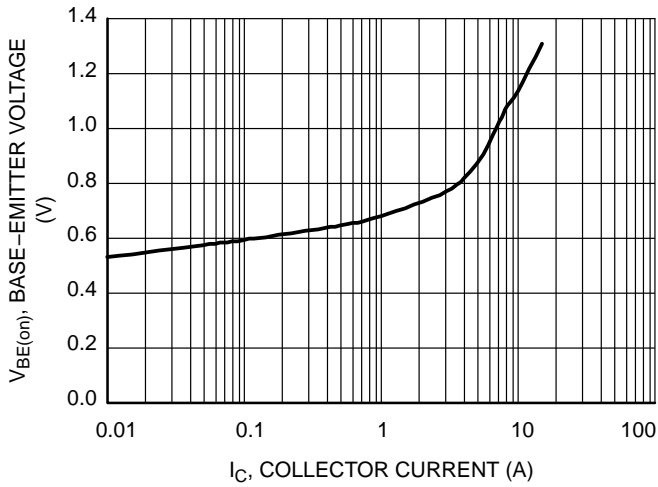
**Figure 5. Typical Saturation Voltage, NPN MJL4281A**



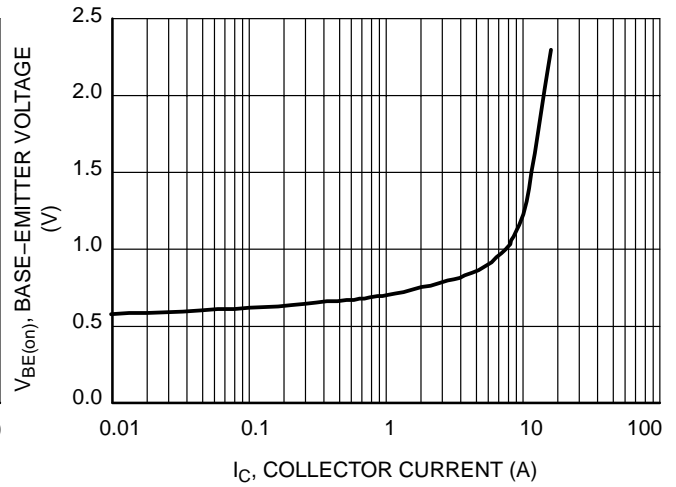
**Figure 6. Typical Saturation Voltage, PNP MJL4302A**

# MJL4281A (NPN) MJL4302A (PNP)

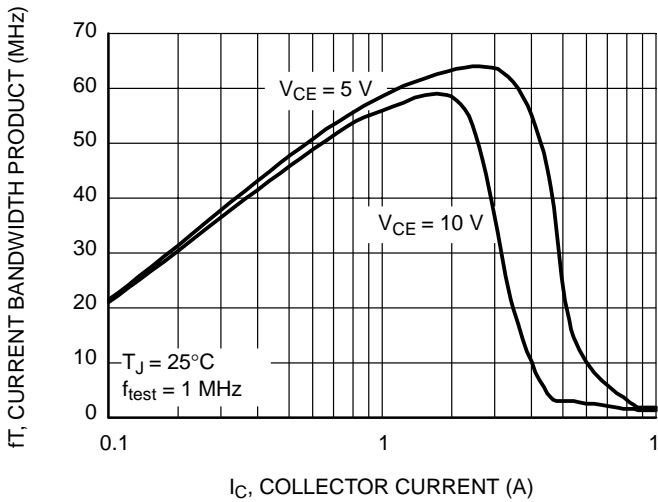
## TYPICAL CHARACTERISTICS



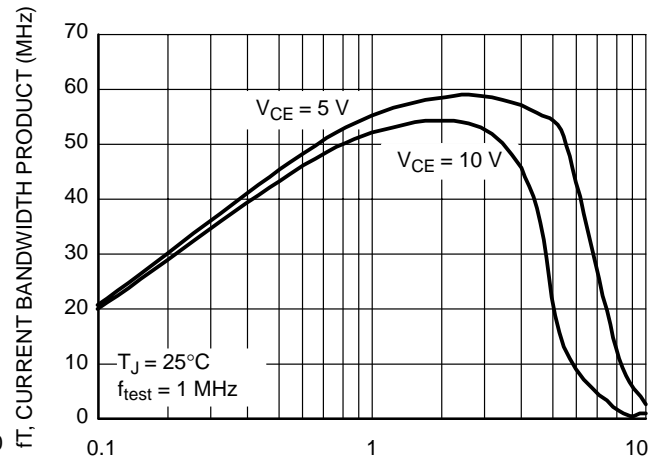
**Figure 7. Typical Base-Emitter Voltages, NPN MJL4281A**



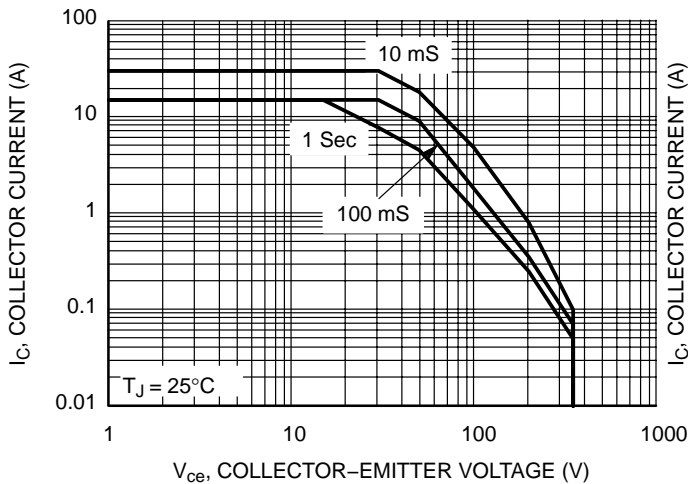
**Figure 8. Typical Base-Emitter Voltages, PNP MJL4302A**



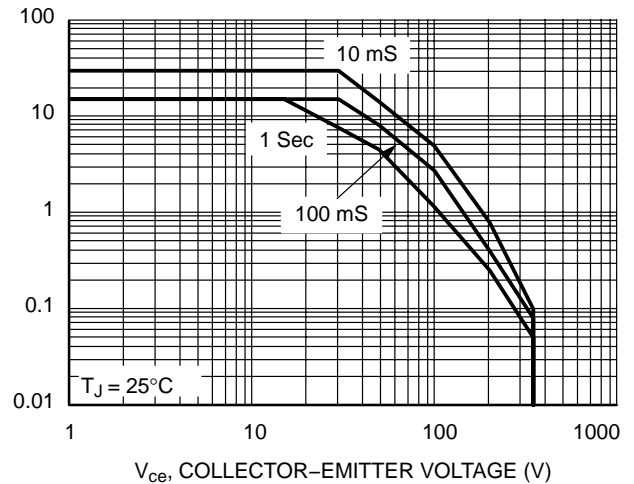
**Figure 9. Typical Current Gain Bandwidth Product, NPN MJL4281A**



**Figure 10. Typical Current Gain Bandwidth Product, PNP MJL4302A**



**Figure 11. Active Region Safe Operating Area, NPN MJL4281A**

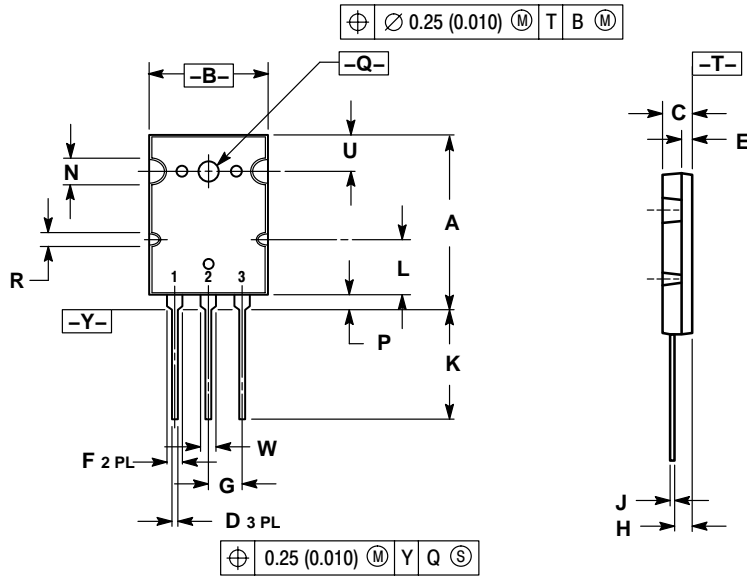


**Figure 12. Active Region Safe Operating Area, PNP MJL4302A**

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## PACKAGE DIMENSIONS

TO-3PBL (TO-264)  
CASE 340G-02  
ISSUE H




- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	28.0	29.0	1.102	1.142
B	19.3	20.3	0.760	0.800
C	4.7	5.3	0.185	0.209
D	0.93	1.48	0.037	0.058
E	1.9	2.1	0.075	0.083
F	2.2	2.4	0.087	0.102
G	5.45 BSC		0.215 BSC	
H	2.6	3.0	0.102	0.118
J	0.43	0.78	0.017	0.031
K	17.6	18.8	0.693	0.740
L	11.0	11.4	0.433	0.449
N	3.95	4.75	0.156	0.187
P	2.2	2.6	0.087	0.102
Q	3.1	3.5	0.122	0.137
R	2.15	2.35	0.085	0.093
U	6.1	6.5	0.240	0.256
W	2.8	3.2	0.110	0.125

- STYLE 2:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER

## MJL4281A (NPN) MJL4302A (PNP)

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